

~~phosphine, and HCL, and boron trichloride~~ comprises exposing the ~~wafer~~ first conductive layer to this selection prior to depositing the second conductive layer.

108. (Previously Presented) The method of claim 88 wherein exposing the wafer to a reducing environment comprises exposing the wafer to silane gas.

109. (Currently Amended) The method of claim 88 wherein exposing the ~~wafer~~ second conductive layer to a material selected from the group consisting of diborane, and HCl comprises exposing the wafer to this selection prior to exposing the ~~wafer~~ second conductive layer to a reducing environment.

110. (Currently Amended) The method of claim 88 wherein exposing the ~~wafer~~ second conductive layer to a material selected from the group consisting of diborane, and HCl comprises exposing the ~~wafer~~ second conductive layer to this selection prior to depositing the second conductive layer.

REMARKS

Claims 80-84 and 88-110 are pending in the present application. In the Office Action dated June 4, 2004, the Examiner rejected claims 80, 81, 88, 89, 96-101 and 105-110 under 35 U.S.C. 103(a) as being unpatentable over Sekine et al. (U.S. Patent No. 5,622,888) in view of Kim et al. (U.S. Patent No. 6,194,263 B1) further in view of Moslehi (U.S. Patent No. 5,089,441) and Yew et al. U.S. Patent No. 5,753,559). Claims 83, 91, 94 and 103 were rejected under 35 U.S.C. 103(a) as being unpatentable over Sekine in view of Kim and further in view of Moslehi as applied to claim 80 or in view of Sekine in view of Yew as applied to claim 80 above, and further in view of Chen et al. (US Patent No. 6,077,742). Claims 82, 84, 90, 92, 95, 102 and 104 were rejected under 35 U.S.C. 103(a) as being unpatentable over Sekine in view of Kim further in view of Moslehi or Sekine in view of Yew as applied to claim 80 above, and further in view of Lee et al. (U.S. Patent No. 2001/0001501A1).

A phone conference was held with the Examiner on July 22, 2004. Applicants and the Examiner agreed that as proposed to be amended, the claims overcome the rejections based upon the cited references. Specifically, the cited references do not teach exposing a

tungsten nitride layer to diborane or HCl as required by the limitations of claims 80 and 81 as proposed to be amended. The cited references also do not teach or suggest passivating a tungsten nitride layer as required by the limitations of claims 88 and 89.

All of the claims remaining in the application are now clearly allowable. Favorable consideration and a Notice of Allowance are earnestly solicited.

Respectfully submitted,

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Enclosures:

Postcard

Fee Transmittal Sheet (+ copy)

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